Supporting Information (SI)

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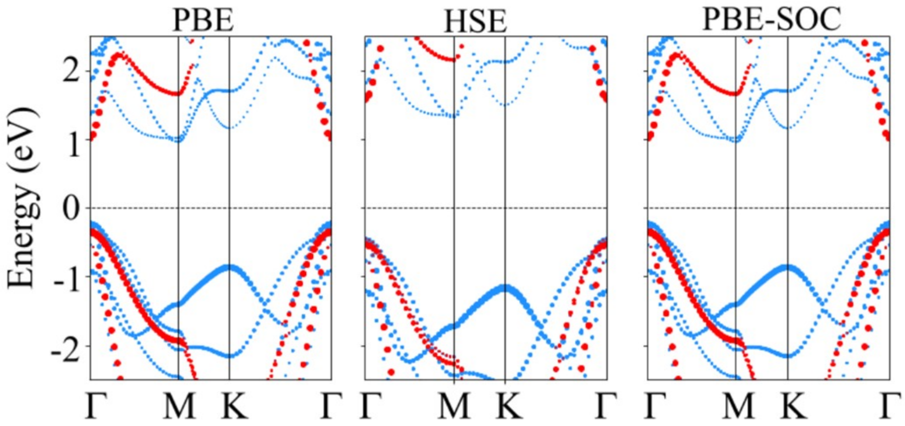

Fig. S1. Projected band structures of the GeH/SiSb heterostructure for the most favorable stacking pattern AB1 obtained by PBE, HSE and PBE-SOC methods.